TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM1213-2L **PRELIMINARY**

FEATURES

- **HIGH POWERT**
 - P1dB=33.5dBm at 12.7GHz to 13.2GHz
- **HIGH GAIN**

G1dB=7.5dB at 12.7GHz to 13.2GHz

■ BROAD BAND INTERNALLY MATCHED

■ HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB	P1dB		dBm	32.5	33.5	
Compression Point						
Power Gain at 1dB	G1dB	VDS= 9V	dB	6.5	7.5	
Compression Point		f= 12.7 to 13.2GHz				
Drain Current	IDS1		Α		0.85	1.1
Gain Flatness	ΔG		dB			±0.8
Power Added Efficiency	ηadd		%		24	
3 rd Order Intermodulation	IM3		dBc	-42	-45	
Distortion		NOTE				
Drain Current	IDS2		Α	_	0.85	1.1
Channel Temperature Rise	ΔTch	VDS X IDS X Rth(c-c)	°C			60

NOTE: Two Tone Test, Po=22dBm (Single Carrier Level)

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V	mS	_	600	_
		IDS= 1.0A				
Pinch-off Voltage	VGSoff	VDS= 3V	V	-2.0	-3.5	-5.0
		IDS= 30mA				
Saturated Drain Current	IDSS	VDS= 3V	Α		2.0	2.6
		VGS= 0V				
Gate-Source Breakdown	VGSO	IGS= -30μA	V	-5		_
Voltage						
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		5.0	6.0

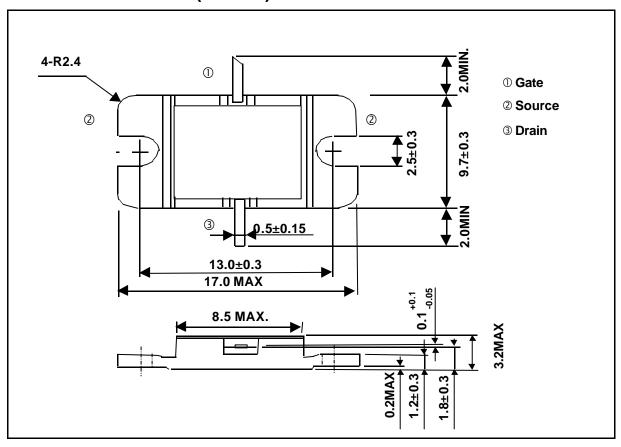
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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	>	-5
Drain Current	IDS	Α	2.6
Total Power Dissipation (Tc= 25 °C)	РТ	W	15
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-9D1B)



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260° C.